Abstracts

GaAsFET Mount Structure Design for 30-GHz-Band Low-Noise Amplifiers

H. Mizuno. "GaAsFET Mount Structure Design for 30-GHz-Band Low-Noise Amplifiers." 1982 Transactions on Microwave Theory and Techniques 30.6 (Jun. 1982 [T-MTT]): 854-858.

This paper describes a GaAsFET mount design method for 30-GHz-band low-noise reflection-type amplifiers with the metal wall as a feedback circuit. Two examples of 30-GHz-band low-noise amplifiers are described; one with wide-band response and the other with high-gain response. The wide-band amplifier has 13-dB gain and 8.5-dB noise figure in the frequency range from 27.5 GHz to 29.1 GHz. The high gain amplifier has 15-dB gain and 9-dB noise figure in the frequency range from 27.7 GHz to 28.7 GHz. These results demonstrate the utility of this design approach.

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